

1N6263W

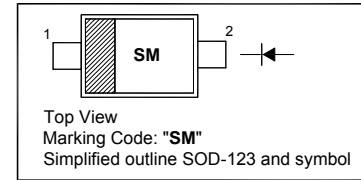
Surface Mount Schottky Barrier Diode

Features

- Low forward voltage
- Low reverse capacitance

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	60	V
Working Peak Reverse Voltage	V_{RWM}	60	V
DC Blocking Voltage	V_R	60	V
RMS Reverse Voltage	$V_{R(RMS)}$	42	V
Average Rectified Forward Current	$I_{F(AV)}$	15	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	50 2	mA A
			at $t = 1\text{ s}$ at $t = 10\text{ }\mu\text{s}$
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	300	$^\circ\text{C}/\text{W}$
Power Dissipation	P_{tot}	333	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	60	-	V
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 15\text{ mA}$	V_F	- -	0.41 1	V
Reverse Current at $V_R = 50\text{ V}$	I_R	-	200	nA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	-	2.2	pF
Reverse Recovery Time at $I_F = I_R = 5\text{ mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	1	ns

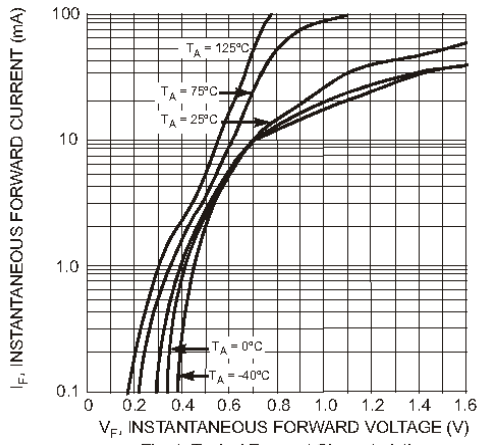


Fig. 1 Typical Forward Characteristics

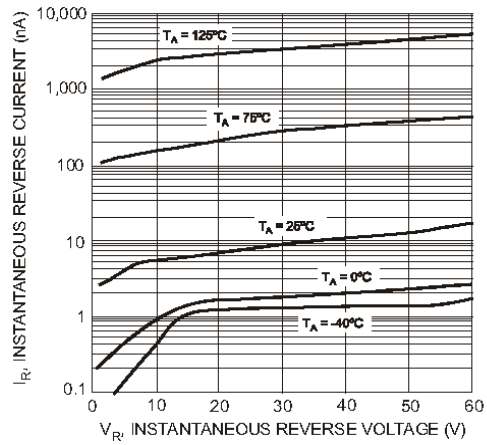


Fig. 2 Typical Reverse Characteristics

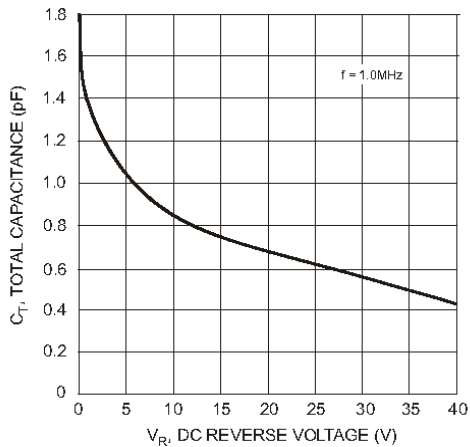
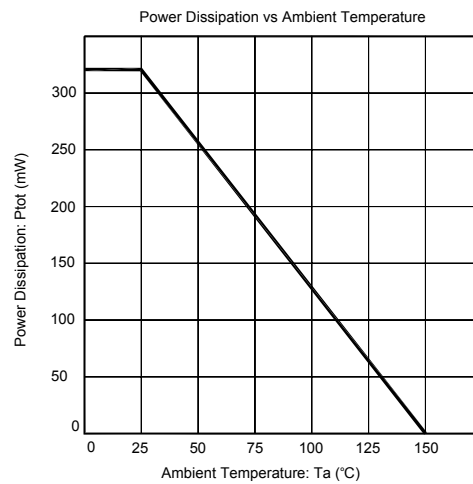


Fig. 3 Total Capacitance vs. Reverse Voltage

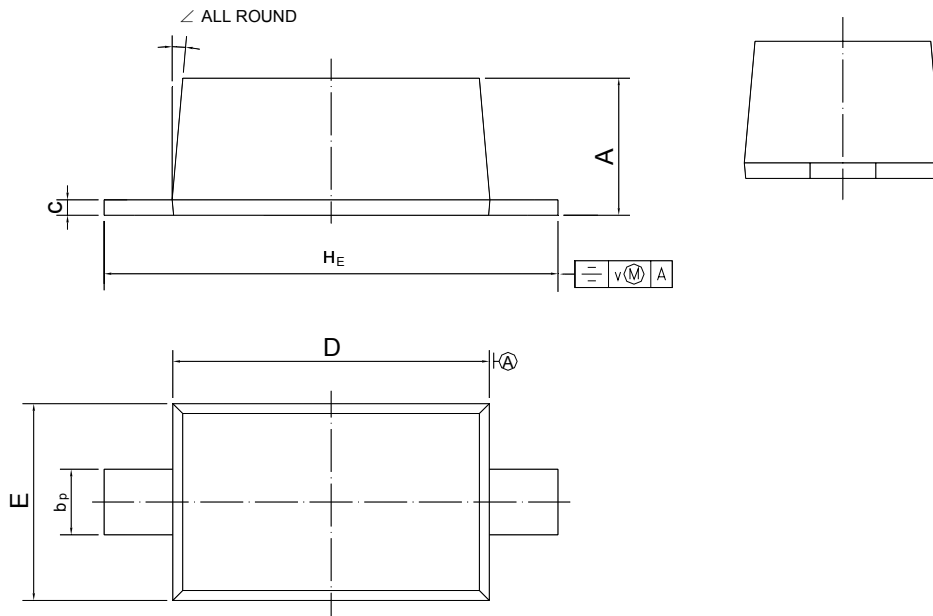


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b _p	c	D	E	H _E	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°